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(54) **LAYOUT METHOD FOR SOFT-ERROR HARD ELECTRONICS, AND RADIATION HARDENED LOGIC CELL**

ANORDNUNGSVERFAHREN FÜR SOFT-ERROR-IMMUNE ELEKTRONIK UND STRAHLUNGSGEHÄRTETE LOGIKZELLE

PROCÉDÉ D'AGENCEMENT DE DISPOSITIFS ÉLECTRONIQUES RÉSISTANT À UNE ERREUR DOUCE, ET CELLULE LOGIQUE DURCIE VIS-À-VIS D'UN RAYONNEMENT

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(74) Representative: **Nguyen Van Yen, Christian et al**

Marks & Clerk France
Conseils en Propriété Industrielle
Immeuble Visium
22, Avenue Aristide Briand
94117 Arcueil Cedex (FR)

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(73) Proprietor: **Lilja, Klas Olof**
Pleasanton, CA 94588 (US)

(72) Inventor: **Lilja, Klas Olof**
Pleasanton, CA 94588 (US)

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